

STT165GKLLB

Thyristor-Thyristor Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_{RRM}, I_{DRM}	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	40	mA
V_T, V_F	$I_T, I_F=300A; T_{VJ}=25^{\circ}C$	1.36	V
V_{TO}	For power-loss calculations only ($T_{VJ}=T_{VJM}$)	0.8	V
r_T		1.6	$m\Omega$
V_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	2 2.6	V
I_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	150 200	mA
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.25	V
I_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	10	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=30\mu s; V_D=6V$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	200	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	150	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.5A; di_G/dt=0.5A/\mu s$	2	μs
t_q	$T_{VJ}=T_{VJM}; I_T=160A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$ typ.	150	μs
Q_s	$T_{VJ}=T_{VJM}; I_T, I_F=300A; -di/dt=50A/\mu s$	550	μC
I_{RM}		235	A
R_{thJC}	per thyristor/diode; DC current per module	0.155 0.0775	K/W
R_{thJK}	per thyristor/diode; DC current per module	0.225 0.1125	K/W
d_s	Creeping distance on surface	12.7	mm
d_A	Creepage distance in air	9.6	mm
a	Maximum allowable acceleration	50	m/s^2

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL file NO.E310749
- * RoHS compliant

APPLICATIONS

- * Motor control
- * Power converter
- * Heat and temperature control for industrial furnaces and chemical processes
- * Lighting control
- * Contactless switches

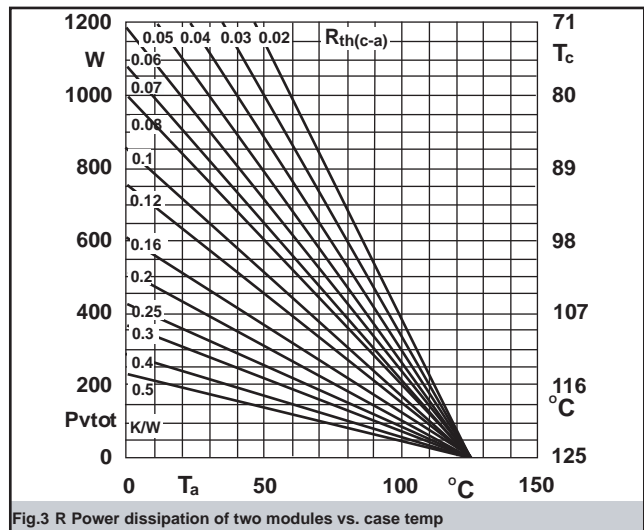
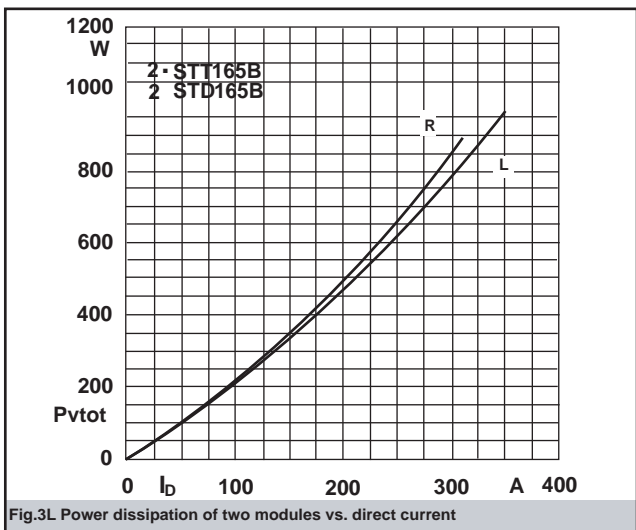
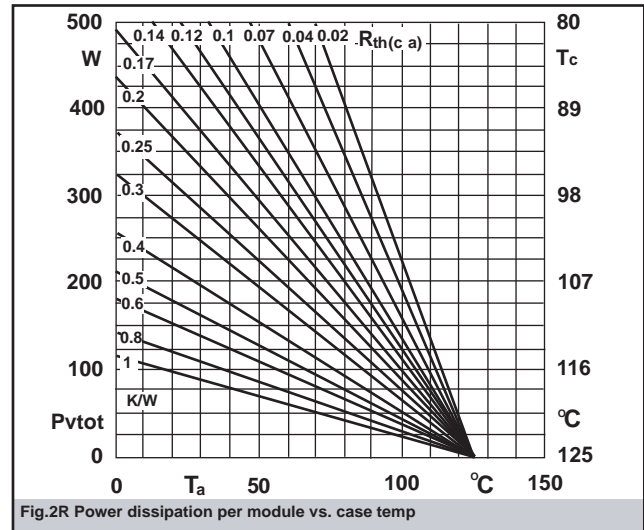
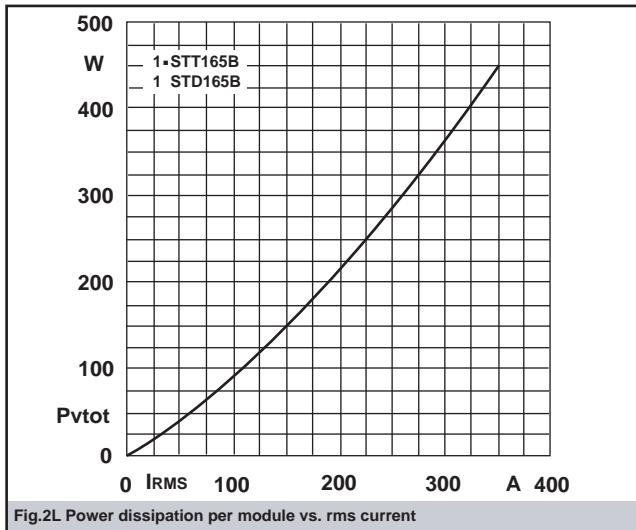
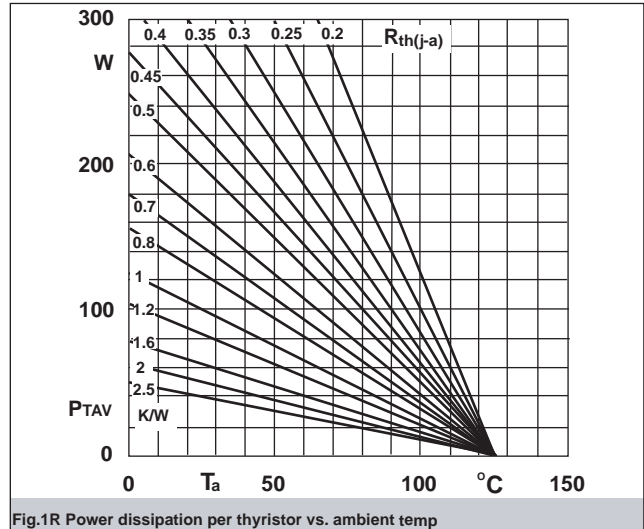
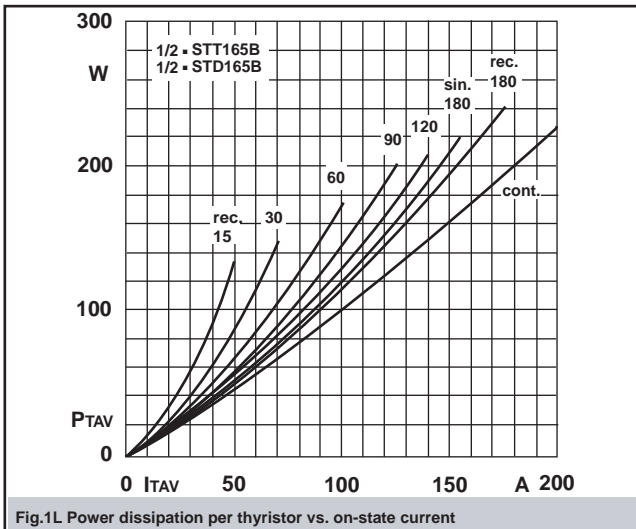
ADVANTAGES

- * Space and weight savings
- * Simple mounting
- * Improved temperature and power cycling
- * Reduced protection circuits

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